



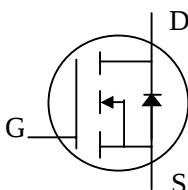
N-channel Enhancement-mode Power MOSFET

Simple Drive Requirement

Fast Switching Characteristic

Lower Gate Charge

RoHS-compliant, halogen-free

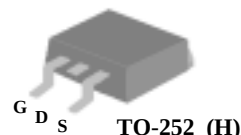


BV_{DS}	100V
$R_{DS(ON)}$	16.5m Ω
I_D	56A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

The AP55T10GH-HF-3 is in the TO-252 package which is widely preferred for commercial and industrial surface mount applications such as medium-power DC/DC converters.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D at $T_C=25^\circ\text{C}$	Continuous Drain Current	56	A
I_D at $T_C=100^\circ\text{C}$	Continuous Drain Current	40	A
I_{DM}	Pulsed Drain Current ¹	160	A
P_D at $T_C=25^\circ\text{C}$	Total Power Dissipation	125	W
P_D at $T_A=25^\circ\text{C}$	Total Power Dissipation ³	2	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	1.2	$^\circ\text{C/W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient (PCB mount) ³	62.5	$^\circ\text{C/W}$

Ordering Information

AP55T10GH-HF-3TR RoHS-compliant halogen-free TO-252 shipped on tape and reel (3000 pcs/reel)



Electrical Specifications at $T_j=25^{\circ}\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=40A$	-	-	16.5	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	5	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=40A$	-	55	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=80V, V_{GS}=0V$	-	-	25	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}= \pm 20V, V_{DS}=0V$	-	-	± 100	nA
Q_g	Total Gate Charge ²	$I_D=40A$	-	63	100	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=80V$	-	23	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	30	-	nC
$t_{d(on)}$	Turn-on Delay Time ²	$V_{DS}=50V$	-	20	-	ns
t_r	Rise Time	$I_D=10A$	-	35	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega$	-	30	-	ns
t_f	Fall Time	$V_{GS}=10V$	-	15	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	3300	5280	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	320	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0MHz$	-	190	-	pF
R_g	Gate Resistance	$f=1.0MHz$	-	1	-	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_S=40A, V_{GS}=0V$	-	-	1.3	V
t_{rr}	Reverse Recovery Time ²	$I_S=10A, V_{GS}=0V$	-	70	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	220	-	nC

Notes:

1. Pulse width limited by maximum junction temperature.
2. Pulse test - pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. Surface-mounted on 1 in² copper pad of FR4 board,

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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Typical Electrical Characteristics

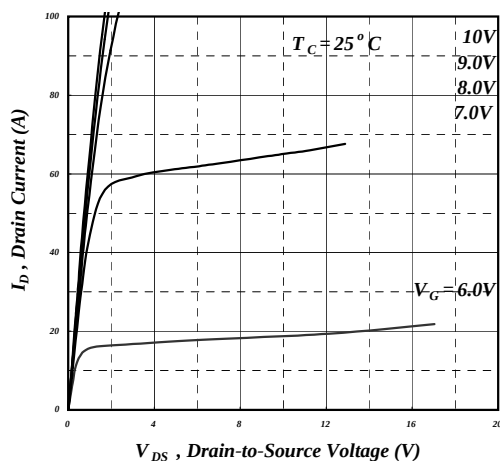


Fig 1. Typical Output Characteristics

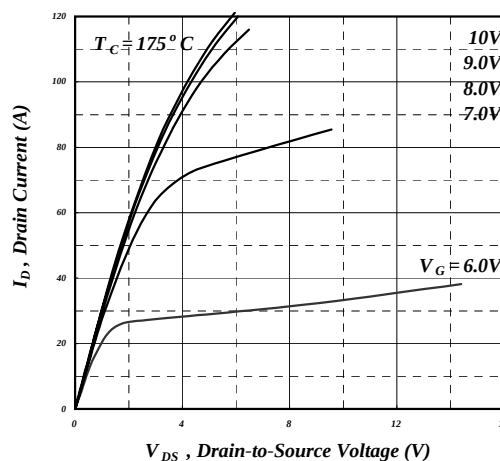


Fig 2. Typical Output Characteristics

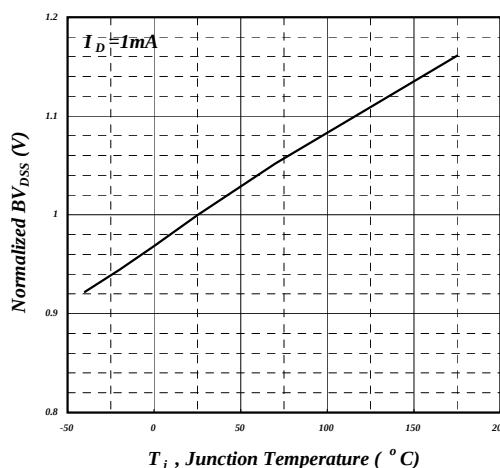


Fig 3. On-Resistance vs. Gate Voltage

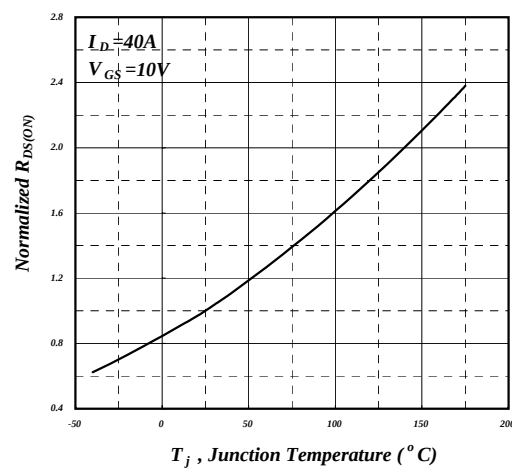


Fig 4. Normalized On-Resistance
vs. Junction Temperature

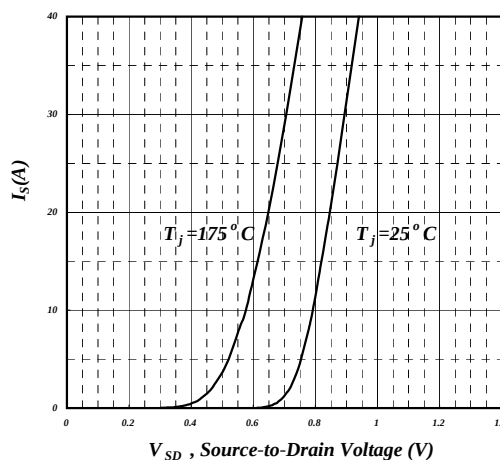


Fig 5. Forward Characteristic of
Reverse Diode

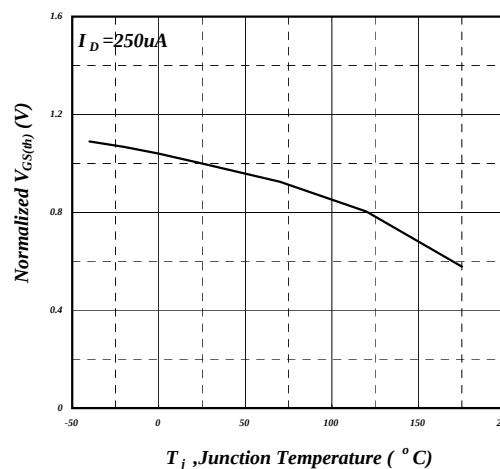


Fig 6. Gate Threshold Voltage vs.
Junction Temperature



Typical Electrical Characteristics (cont.)

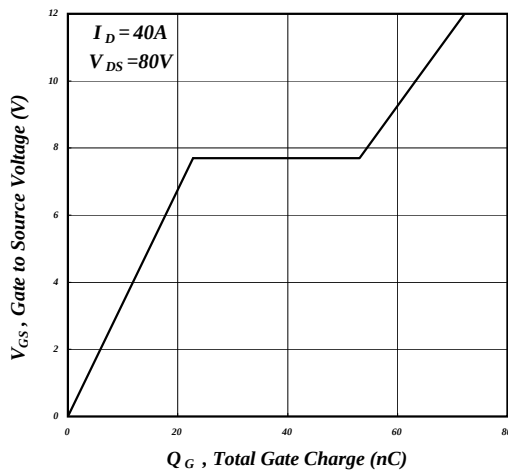


Fig 7. Gate Charge Characteristics

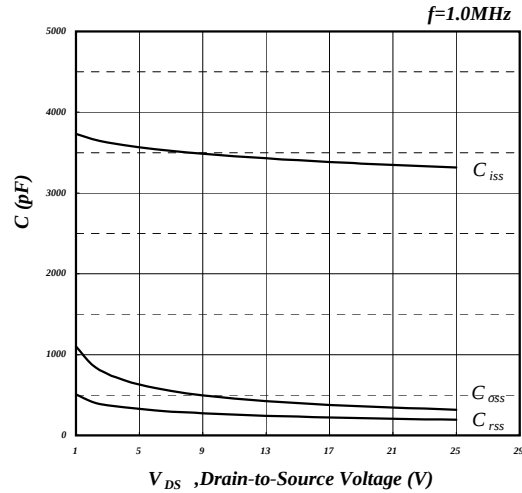


Fig 8. Typical Capacitance Characteristics

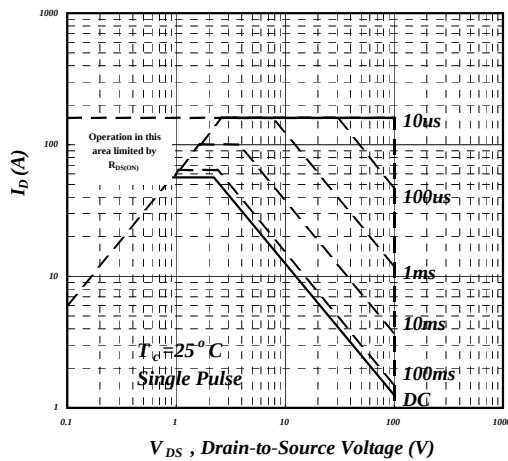


Fig 9. Maximum Safe Operating Area

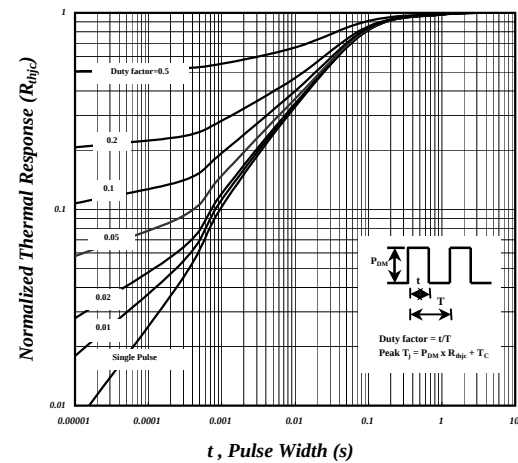


Fig 10. Effective Transient Thermal Impedance

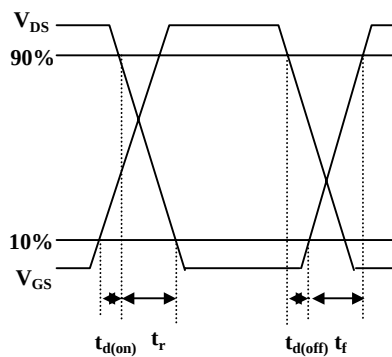


Fig 11. Switching Time Waveforms

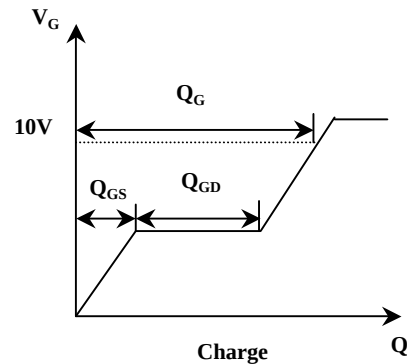
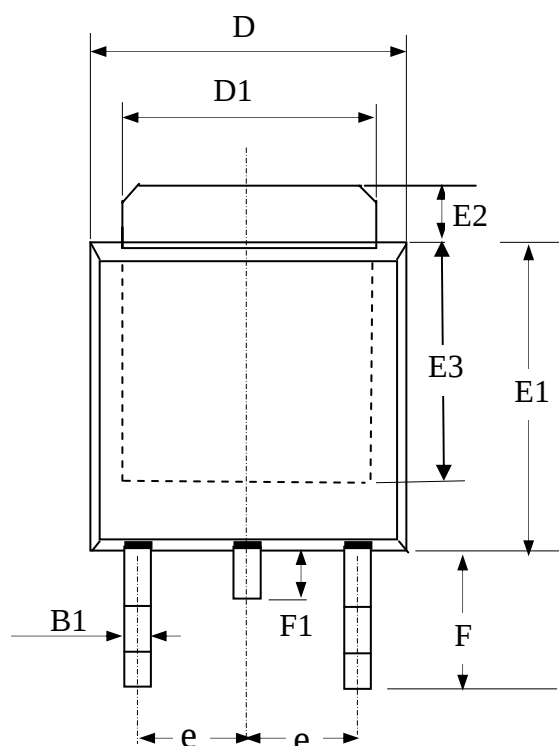


Fig 12. Gate Charge Waveform

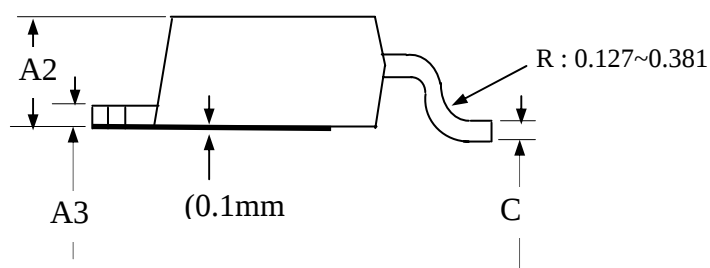


Package Dimensions: TO-252



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A2	1.80	2.30	2.80
A3	0.40	0.50	0.60
B1	0.40	0.70	1.00
D	6.00	6.50	7.00
D1	4.80	5.35	5.90
E3	3.50	4.00	4.50
F	2.20	2.63	3.05
F1	0.50	0.85	1.20
E1	5.10	5.70	6.30
E2	0.50	1.10	1.80
e	--	2.30	--
C	0.35	0.50	0.65

1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.



Marking Information: TO-252

Laser Marking

